

Features

- 10 mm X 10 mm active area
- Low dark current & capacitance
- Fast rise times
- High QE at 1064 nm

Description

100 mm² 1064 nm enhanced PIN Photodiode. Packaged in a black surface mount ceramic with a fused silica window.

Applications

- Pulsed 1064 nm laser detection
- NIR pulsed light sensor
- High speed photometry

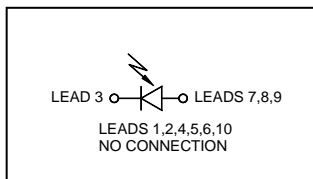
RoHS

2011/65/EU

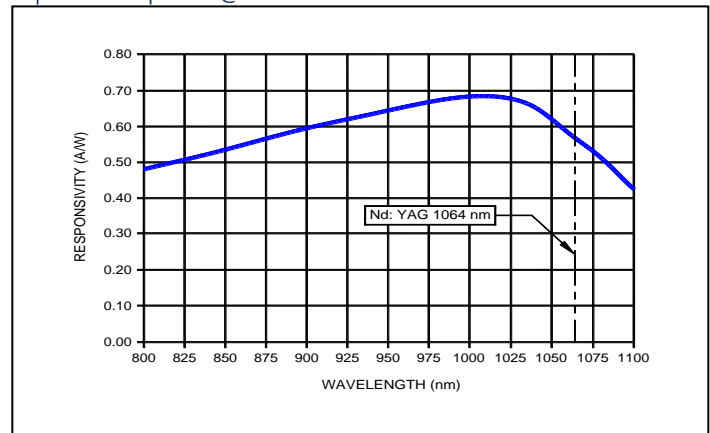
Absolute maximum ratings

Symbol	Parameter	Min	Max	Unit
T _{STG}	Storage Temp	-20	+80	°C
T _{OP}	Operating Temp	-20	+60	°C
V _{R(OP)}	Reverse Operating Voltage	-	150	V
I _(PEAK)	Peak DC Current	-	10	mA

Schematic



Spectral response @ 23°C



Electro-optical characteristics @ 23° C

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
I _D	Dark Current	V _R = 150 V; @ 23°C	---	80	---	nA
		V _R = 150 V; @ 60°C	---	1.2	---	μA
C	Capacitance	V _R = 150 V	---	100	---	pF
	Responsivity	V _R = 150 V; λ = 1010 nm; @ 23°C	---	0.68	---	A/W
		V _R = 150 V; λ = 1064 nm; @ 23°C	---	0.56	---	
V _{BR}	Breakdown Voltage	I _R = 10 μA	200	---	---	V
t _r	Rise Time	V _R = 150 V; λ = 1064 nm; R _L = 50 Ω	---	6	---	ns

Disclaimer: Due to our policy of continued development, specifications are subject to change without notice.
Package is not suitable for reflow soldering.